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Sheet 3 of 12

Form 1449*

INFORMATION DISCLOSURE STATEMENT
BY APPLICANT
(Use several sheets if necessary)

Atty. Docket No.: 303.389US2

Serial No. Unknown

Applicant: Leonard Forbes et al.

Filing Date: Herewith

Group: Unknown

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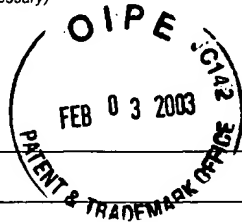
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Complete if Known

Application Number 09/467992

Filing Date December 20, 1999

First Named Inventor Forbes, Leonard

Group Art Unit 2815

Examiner Name Lee, Eugene

Sheet 1 of 1

Attorney Docket No: 303.389US2

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